

# TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)



ON Semiconductor®

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## Complementary Silicon Plastic Power Transistors

Designed for use in general purpose amplifier and switching applications.

### Features

- High Current Gain – Bandwidth Product
- Compact TO–220 Package
- These Devices are Pb–Free and are RoHS Compliant\*

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	$V_{CEO}$	40 60 80 100	Vdc
Collector–Base Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	$V_{CB}$	40 60 80 100	Vdc
Emitter–Base Voltage	$V_{EB}$	5.0	Vdc
Collector Current – Continuous	$I_C$	3.0	Adc
Collector Current – Peak	$I_{CM}$	5.0	Adc
Base Current	$I_B$	1.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	40 0.32	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	2.0 0.016	W W/ $^\circ\text{C}$
Unclamped Inductive Load Energy (Note 1)	E	32	mJ
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–65 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

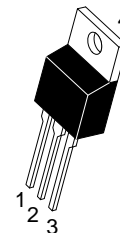
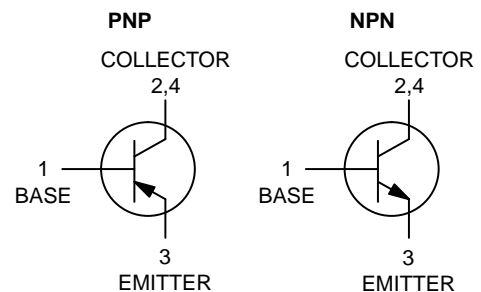
1.  $I_C = 1.8\text{ A}$ ,  $L = 20\text{ mH}$ , P.R.F. = 10 Hz,  $V_{CC} = 10\text{ V}$ ,  $R_{BE} = 100\ \Omega$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	3.125	$^\circ\text{C/W}$

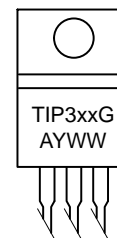
\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 3 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 40–60–80–100 VOLTS, 40 WATTS



TO-220  
CASE 221A  
STYLE 1

### MARKING DIAGRAM



TIP3xx = Device Code  
xx = 1, 1A, 1B, 1C,  
2, 2A, 2B, 2C,  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb–Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

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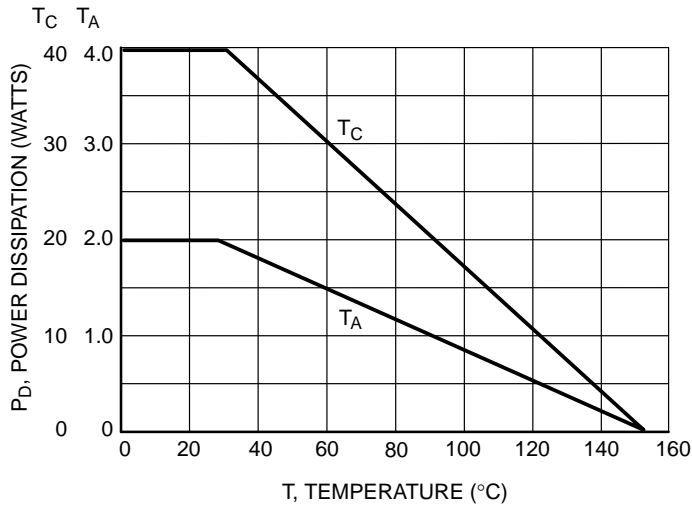
## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Sustaining Voltage (Note 2) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0) TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	V <sub>CEO(sus)</sub>	40 60 80 100	- - - -	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, I <sub>B</sub> = 0) TIP31G, TIP32G, TIP31AG, TIP32AG (V <sub>CE</sub> = 60 Vdc, I <sub>B</sub> = 0) TIP31BG, TIP31CG, TIP32BG, TIP32CG	I <sub>CEO</sub>	- -	0.3 0.3	mAdc
Collector Cutoff Current (V <sub>CE</sub> = 40 Vdc, V <sub>EB</sub> = 0) TIP31G, TIP32G (V <sub>CE</sub> = 60 Vdc, V <sub>EB</sub> = 0) TIP31AG, TIP32AG (V <sub>CE</sub> = 80 Vdc, V <sub>EB</sub> = 0) TIP31BG, TIP32BG (V <sub>CE</sub> = 100 Vdc, V <sub>EB</sub> = 0) TIP31CG, TIP32CG	I <sub>CES</sub>	- - - -	200 200 200 200	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	1.0	mAdc
<b>ON CHARACTERISTICS (Note 2)</b>				
DC Current Gain (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 4.0 Vdc) (I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 4.0 Vdc)	h <sub>FE</sub>	25 10	- 50	-
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 3.0 Adc, I <sub>B</sub> = 375 mAdc)	V <sub>CE(sat)</sub>	-	1.2	Vdc
Base-Emitter On Voltage (I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 4.0 Vdc)	V <sub>BE(on)</sub>	-	1.8	Vdc
<b>DYNAMIC CHARACTERISTICS</b>				
Current-Gain – Bandwidth Product (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)	f <sub>T</sub>	3.0	-	MHz
Small-Signal Current Gain (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	20	-	-

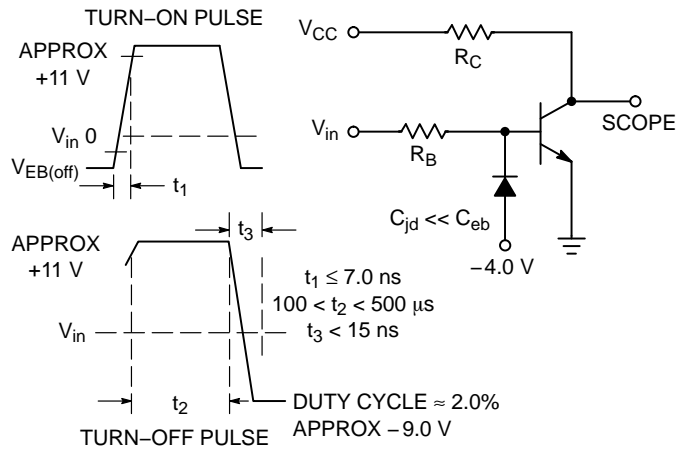
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

**TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)**

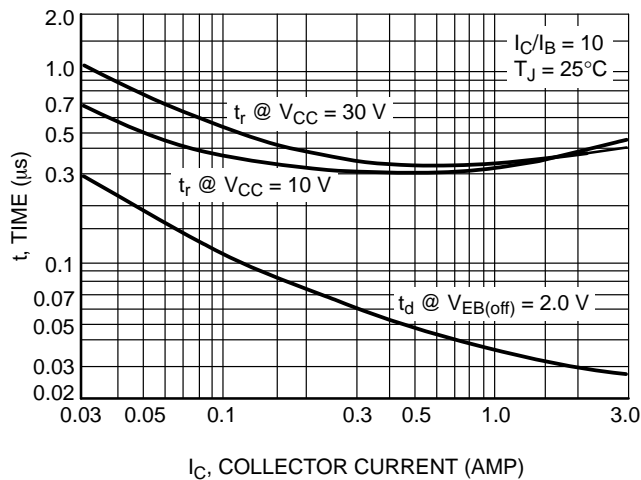


**Figure 1. Power Derating**



$R_B$  and  $R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS.

**Figure 2. Switching Time Equivalent Circuit**



**Figure 3. Turn-On Time**

TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

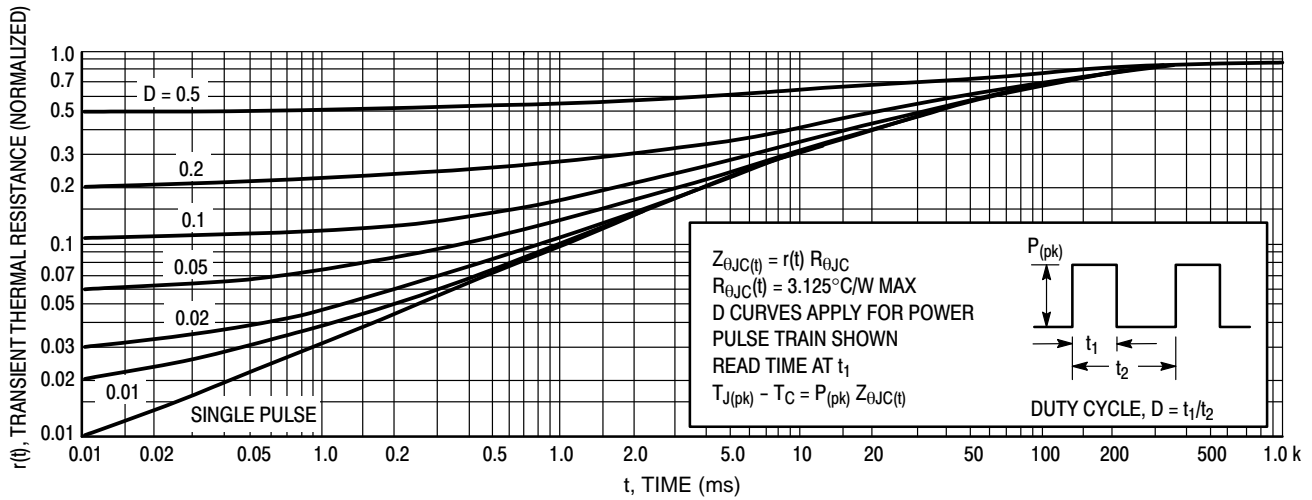


Figure 4. Thermal Response

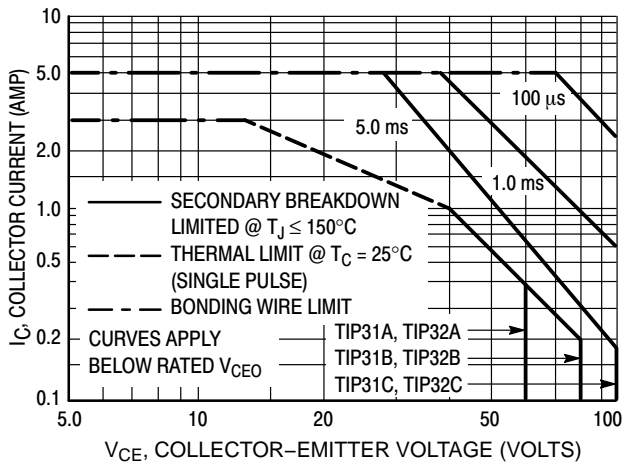


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

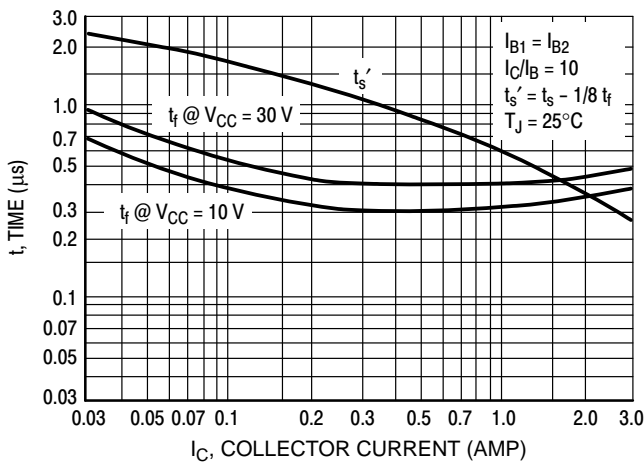


Figure 6. Turn-Off Time

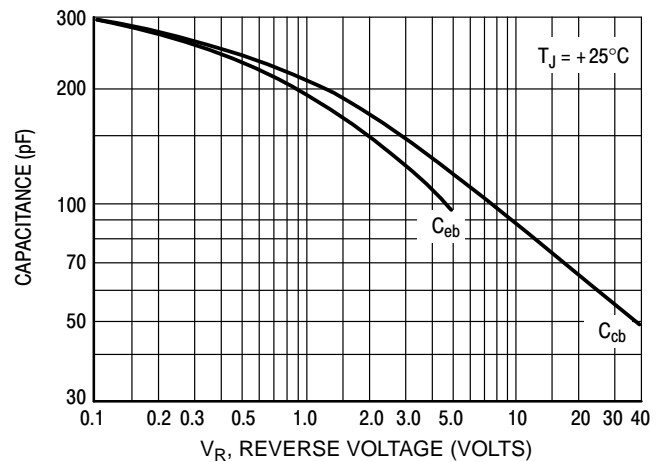
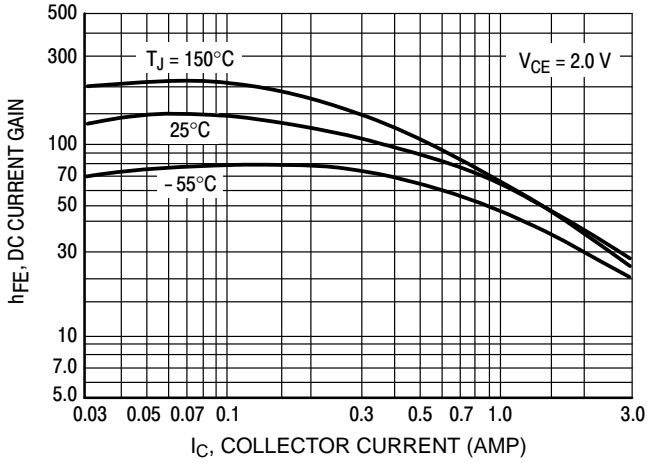
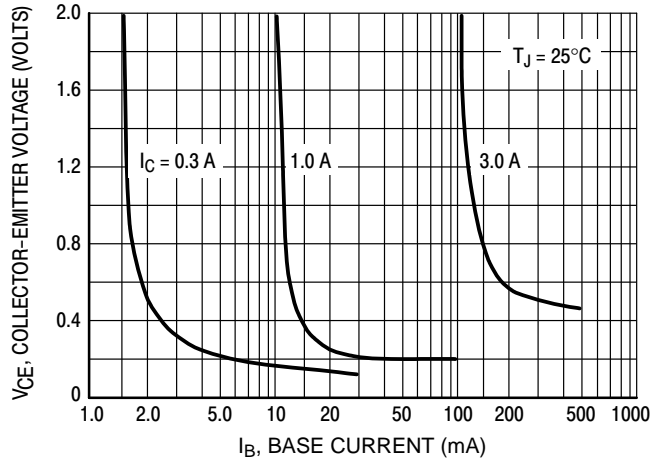


Figure 7. Capacitance

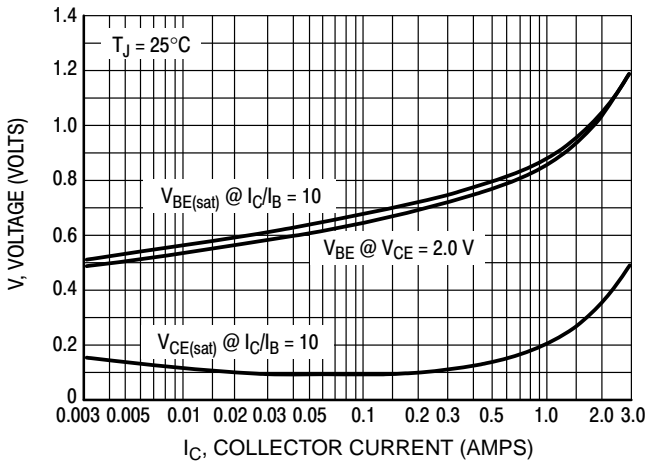
**TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)**



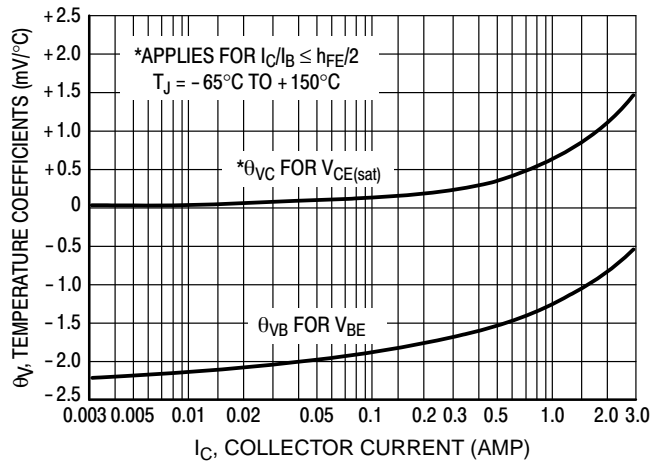
**Figure 8. DC Current Gain**



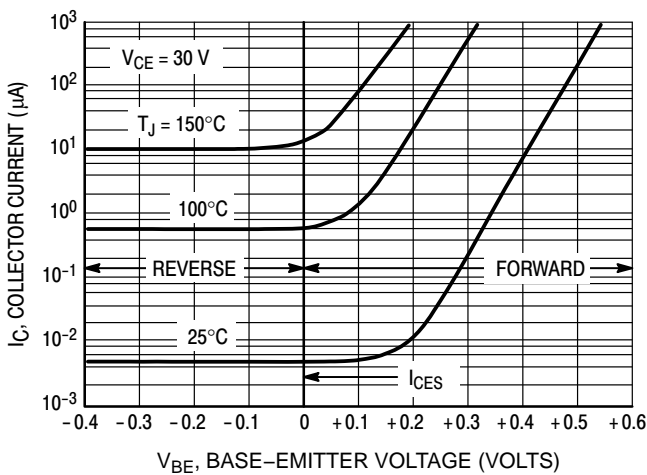
**Figure 9. Collector Saturation Region**



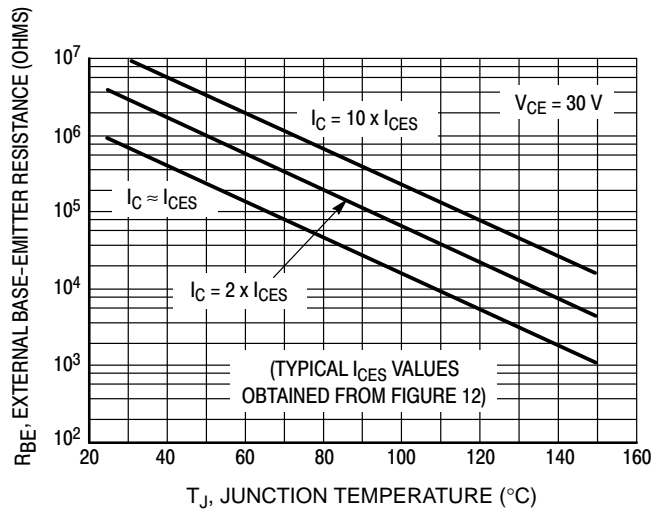
**Figure 10. "On" Voltages**



**Figure 11. Temperature Coefficients**



**Figure 12. Collector Cut-Off Region**



**Figure 13. Effects of Base-Emitter Resistance**

**TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG,  
TIP32CG (PNP)**

**ORDERING INFORMATION**

<b>Device</b>	<b>Package</b>	<b>Shipping</b>
TIP31G	TO-220 (Pb-Free)	50 Units / Rail
TIP31AG	TO-220 (Pb-Free)	50 Units / Rail
TIP31BG	TO-220 (Pb-Free)	50 Units / Rail
TIP31CG	TO-220 (Pb-Free)	50 Units / Rail
TIP32G	TO-220 (Pb-Free)	50 Units / Rail
TIP32AG	TO-220 (Pb-Free)	50 Units / Rail
TIP32BG	TO-220 (Pb-Free)	50 Units / Rail
TIP32CG	TO-220 (Pb-Free)	50 Units / Rail

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